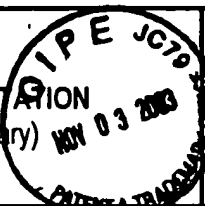


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				ATTY DOCKET NO. ITO.0050US (P16247)		SERIAL NO. 10/633,869			
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U.S. PATENT DOCUMENTS									
EXAMINER INITIAL	A.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE		
	A.								
	B.								
	C.								
	D.								
FOREIGN PATENT DOCUMENTS									
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	E.								
	F.								
	G.								
	H.								
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)									
PD	I.	Hwang, Y.N., Hong, J.S., Lee, S.H., Ahn, S.J., Jeong, G.T., Koh, G.H., Kim, H.J., Jeong, W.C., Lee, S.Y., Park, J.H., Ryoo, K.C., Horii, H., Ha, Y.H., Yi, J.H., Cho, W.Y., Kim, Y.T., Lee, K.H., Joo, S.H., Park, S.O., Jeong, U.I., Jeong, H.S. and Kim, Kinam, "Completely CMOS-Compatible Phase-Change Nonvolatile RAM Using NMOS Cell Transistors," presented at 2003 19 th IEEE Non-Volatile Semiconductor Memory Workshop, Monterey, California, February 26-20, 2003							
PD	J.	Ha, Y.H., Yi, J.H., Horii, H., Park, J.H., Joo, S.H., Park, S.O., Chung, U-In and Moon, J.T., "An Edge Contact Type Cell for Phase Change RAM Featuring Very Low Power Consumption," presented at IEEE 2003 Symposium on VLSI Technology, Kyoto, Japan, June 12-14, 2003							
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	M.								
	N.								
	O.								
EXAMINER				DATE CONSIDERED					
PHUCT. DANG				1/27/05					
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